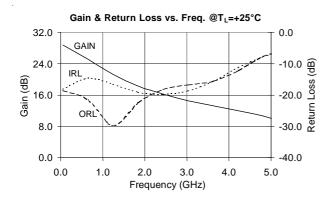


Product Description

The SGA-4586 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring 1 micron emitters provides high FT and excellent thermal perfomance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only 2 DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants.



SGA-4586



DC-4000 MHz, Cascadable **SiGe HBT MMIC Amplifier**



Product Features

- •Now available in Lead Free. RoHS Compliant, & Green Packaging
- High Gain: 17.9 dB at 1950 MHz
- Cascadable 50 Ohm
- Operates From Single Supply
- Low Thermal Resistance Package

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- · Wireless Data, Satellite

 $Z_0 = Z_1 = 50 \text{ Ohms}$

Symbol	Parameter	Units	Frequency	Min.	Тур.	Max.
G	Small Signal Gain	dB dB dB	850 MHz 1950 MHz 2400 MHz	22.0	24.0 17.9 16.3	26.5
P _{1dB}	Output Power at 1dB Compression	dBm dBm	850 MHz 1950 MHz		16.5 13.7	
OIP ₃	Output Third Order Intercept Point	dBm dBm	850 MHz 1950 MHz		28.6 27.7	
Bandwidth	Determined by Return Loss (>10dB)	MHz			4000	
IRL	Input Return Loss	dB	1950 MHz		19.4	
ORL	Output Return Loss	dB	1950 MHz		21.5	
NF	Noise Figure	dB	1950 MHz		1.9	
V_{D}	Device Operating Voltage	V			3.6	
I _D	Device Operating Current	mA		41	45	49
R _{TH} , j-I	Thermal Resistance (junction to lead)	°C/W			97	
Test Condit	Fest Conditions: $V_s = 8 \text{ V}$ $I_D = 45 \text{ mA Typ.}$ OIP ₃ Tone Spacing = 1 MHz, Pout per tone =					

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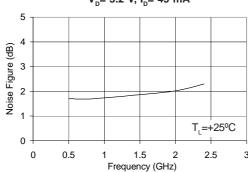
 $R_{BIAS} = 100 Ohms$

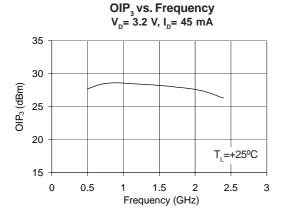


Typical RF Performance at Key Operating Frequencies

			Frequency (MHz)					
Symbol	Parameter	Unit	100	500	850	1950	2400	3500
G	Small Signal Gain	dB		26.2	24.0	18.0	16.3	
OIP ₃	Output Third Order Intercept Point	dBm		27.7	28.6	26.0	26.3	
P _{1dB}	Output Power at 1dB Compression	dBm		16.3	16.5	14.0	12.7	
IRL	Input Return Loss	dB	18.1	14.9	15.0	19.4	19.8	16.1
ORL	Output Return Loss	dB	18.5	20.6	24.4	21.5	18.3	16.1
S ₁₂	Reverse Isolation	dB	30.1	28.4	26.6	21.2	19.3	15.8
NF	Noise Figure	dB		1.7	1.7	1.9	2.3	
Test Conditions: $V_s = 8 \text{ V}$ $I_D = 45 \text{ mA}$ Typ. OIP_3 Tone Spacing = 1 MHz, Pout per tone = -5 dB				-5 dBm				

Noise Figure vs. Frequency $V_p = 3.2 \text{ V}, I_p = 45 \text{ mA}$



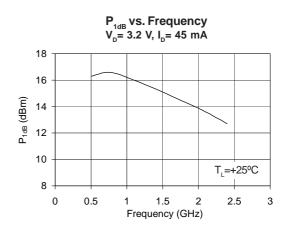


Absolute Maximum Ratings

Parameter	Absolute Limit	
Max. Device Current (I _D)	90 mA	
Max. Device Voltage (V _D)	5 V	
Max. RF Input Power	+18 dBm	
Max. Junction Temp. (T _J)	+150°C	
Operating Temp. Range (T _L)	-40°C to +85°C	
Max. Storage Temp.	+150°C	

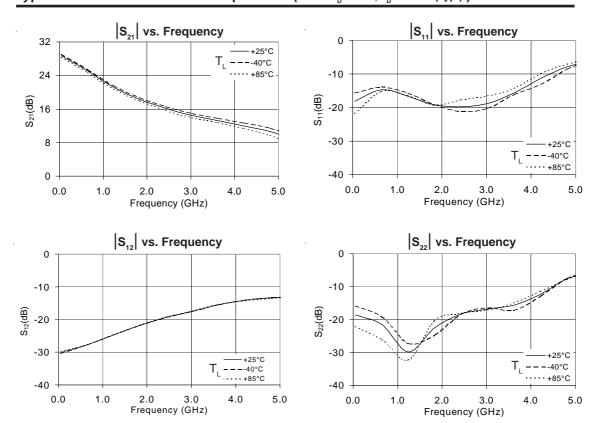
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias conditions should also satisfy the following expression: $I_{_{D}}V_{_{D}}\!<(T_{_{J}}\!-T_{_{L}})\:/\:R_{_{TH'}}\:j\text{-}I$





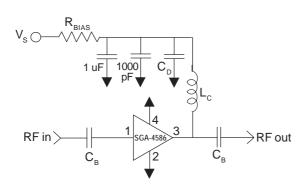
Typical RF Performance Over Temperature (Bias: $V_D = 3.2 \text{ V}$, $I_D = 45 \text{ mA}$ (Typ.))

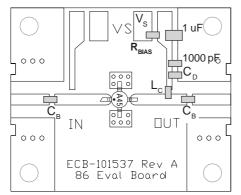


NOTE: Full S-parameter data available at www.sirenza.com

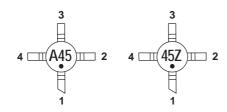


Basic Application Circuit





Part Identification Marking





Caution: ESD sensitive

Appropriate precautions in handling, packaging and testing devices must be observed.

See Application Note AN-075 for Package Outline Drawing

Application Circuit Element Values

Reference	Frequency (Mhz)						
Designator	500	850	1950	2400	3500		
C _B	220 pF	100 pF	68 pF	56 pF	39 pF		
C _D	100 pF	68 pF	22 pF	22 pF	15 pF		
L _c	68 nH	33 nH	22 nH	18 nH	15 nH		

Recommended Bias Resistor Values for $I_D=45$ mA $R_{BIAS}=(V_S-V_D)/I_D$				
Supply Voltage(V _s)	6 V	8 V	10 V	12 V
R _{BIAS} 51 Ω 100 Ω 150 Ω 180 Ω				
Note: R provides DC bias stability over temperature.				

Mounting Instructions

- Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
- We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Pin #	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.
3	RF OUT/ BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.

Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SGA-4586	13"	3000
SGA-4586Z	13"	3000



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